# **General Purpose Transistors**

# **NPN Silicon**

#### **Features**

• Pb-Free Packages are Available\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CEO</sub>	40	Vdc
Collector - Base Voltage	V <sub>CBO</sub>	60	Vdc
Emitter - Base Voltage	V <sub>EBO</sub>	6.0	Vdc
Collector Current - Continuous	I <sub>C</sub>	200	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	625 5.0	mW mW/°C
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

# THERMAL CHARACTERISTICS (Note 1)

Characteristic	Symbol	Max	Unit	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W	

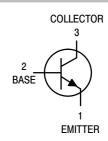
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

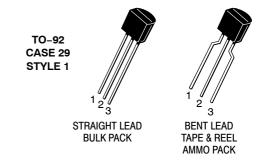
1. Indicates Data in addition to JEDEC Requirements.



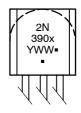
# ON Semiconductor®

http://onsemi.com





#### **MARKING DIAGRAMS**



x = 3 or 4

Y = Year

WW = Work Week
■ = Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

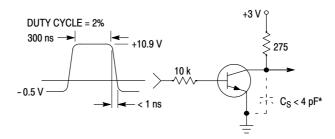
Characteristic			Symbol	Min	Max	Unit
OFF CHARACTERIS	STICS					
Collector – Emitter Breakdown Voltage (Note 2) (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)			V <sub>(BR)CEO</sub>	40	-	Vdc
Collector – Base Breakdown Voltage ( $I_C = 10 \mu Adc$ , $I_E = 0$ )			V <sub>(BR)CBO</sub>	60	-	Vdc
Emitter – Base Break	xdown Voltage (I <sub>E</sub> = 10 μAdc, I <sub>C</sub> = 0)		V <sub>(BR)EBO</sub>	6.0	-	Vdc
Base Cutoff Current	(V <sub>CE</sub> = 30 Vdc, V <sub>EB</sub> = 3.0 Vdc)		I <sub>BL</sub>	_	50	nAdc
Collector Cutoff Curi	rent (V <sub>CE</sub> = 30 Vdc, V <sub>EB</sub> = 3.0 Vdc)		I <sub>CEX</sub>	-	50	nAdc
ON CHARACTERIS	TICS	'		1	·I.	1
DC Current Gain (No (I <sub>C</sub> = 0.1 mAdc, V <sub>CE</sub>		2N3903 2N3904	h <sub>FE</sub>	20 40	_ _	-
( $I_C$ = 1.0 mAdc, $V_{CE}$	= 1.0 Vdc)	2N3904 2N3903 2N3904		35 70	_ _ _	
( $I_C$ = 10 mAdc, $V_{CE}$	= 1.0 Vdc)	2N3903 2N3904		50 100	150 300	
(I $_{C}$ = 50 mAdc, V $_{CE}$	= 1.0 Vdc)	2N3903		30	_	
$(I_C = 100 \text{ mAdc}, V_{CE})$	<u>=</u> = 1.0 Vdc)	2N3904 2N3903 2N3904		60 15 30	- - -	
Collector – Emitter S ( $I_C = 10 \text{ mAdc}, I_B = 10 \text{ mAdc}$ ) ( $I_C = 50 \text{ mAdc}, I_B = 10 \text{ mAdc}$ )			V <sub>CE(sat)</sub>	- -	0.2 0.3	Vdc
Base – Emitter Saturation Voltage (Note 2) (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 1.0 mAdc) (I <sub>C</sub> = 50 mAdc, I <sub>B</sub> = 5.0 mAdc)			V <sub>BE(sat)</sub>	0.65	0.85 0.95	Vdc
SMALL-SIGNAL CI	HARACTERISTICS	'		1	I.	
Current – Gain – Bar (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub>	ndwidth Product = 20 Vdc, f = 100 MHz)	2N3903 2N3904	f <sub>T</sub>	250 300	- -	MHz
Output Capacitance	(V <sub>CB</sub> = 5.0 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)		C <sub>obo</sub>	_	4.0	pF
Input Capacitance (\	V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)		C <sub>ibo</sub>	_	8.0	pF
Input Impedance (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)  2N390 2N390			h <sub>ie</sub>	1.0 1.0	8.0 10	kΩ
Voltage Feedback Ratio (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz) 2N3903 2N3904			h <sub>re</sub>	0.1 0.5	5.0 8.0	X 10 <sup>-4</sup>
Small-Signal Current Gain         (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)         2N3903 2N3904			h <sub>fe</sub>	50 100	200 400	-
Output Admittance (	$I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 1.0 \text{ kHz})$		h <sub>oe</sub>	1.0	40	μmhos
Noise Figure (I <sub>C</sub> = 100 $\mu$ Adc, V <sub>CE</sub> = 5.0 Vdc, R <sub>S</sub> = 1.0 k $\Omega$ , f = 1.0 kHz) 2N3903 2N3904			NF	- -	6.0 5.0	dB
SWITCHING CHARA	ACTERISTICS					
Delay Time	(V <sub>CC</sub> = 3.0 Vdc, V <sub>BE</sub> = 0.5 Vdc,		t <sub>d</sub>	-	35	ns
Rise Time	I <sub>C</sub> = 10 mAdc, I <sub>B1</sub> = 1.0 mAdc)		t <sub>r</sub>	-	35	ns
Storage Time	$(V_{CC} = 3.0 \text{ Vdc}, I_{C} = 10 \text{ mAdc}, I_{B1} = I_{B2} = 1.0 \text{ mAdc})$	2N3903 2N3904	t <sub>s</sub>	- -	175 200	ns
Fall Time	1	ļ	t <sub>f</sub>	_	50	ns

<sup>2.</sup> Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2%.

#### **ORDERING INFORMATION**

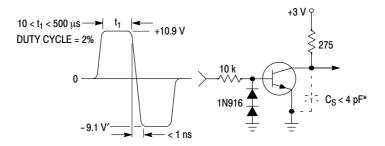
Device	Package	Shipping <sup>†</sup>
2N3903RLRM	TO-92	2000 / Ammo Pack
2N3904	TO-92	5000 Units / Bulk
2N3904G	TO-92 (Pb-Free)	5000 Units / Bulk
2N3904RLRA	TO-92	2000 / Tape & Reel
2N3904RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3904RLRM	TO-92	2000 / Ammo Pack
2N3904RLRMG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N3904RLRP	TO-92	2000 / Ammo Pack
2N3904RLRPG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N3904RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3904ZL1	TO-92	2000 / Ammo Pack
2N3904ZL1G	TO-92 (Pb-Free)	2000 / Ammo Pack

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



\* Total shunt capacitance of test jig and connectors

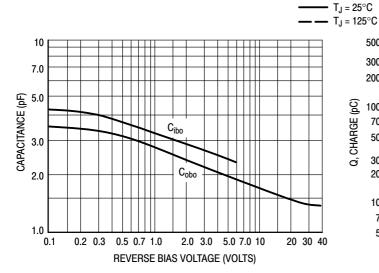
Figure 1. Delay and Rise Time Equivalent Test Circuit



\* Total shunt capacitance of test jig and connectors

Figure 2. Storage and Fall Time Equivalent Test Circuit

#### TYPICAL TRANSIENT CHARACTERISTICS



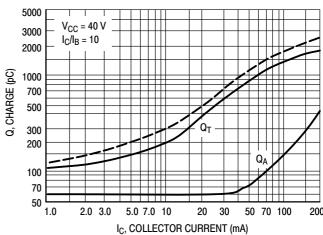
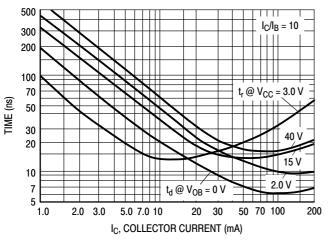


Figure 3. Capacitance

Figure 4. Charge Data



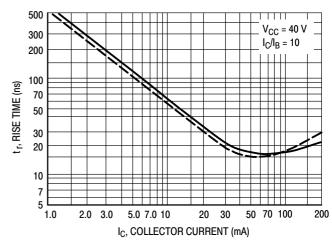
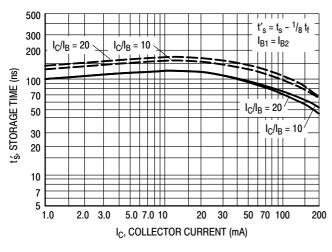


Figure 5. Turn-On Time

Figure 6. Rise Time



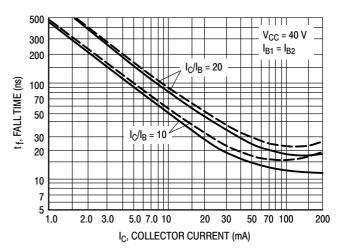
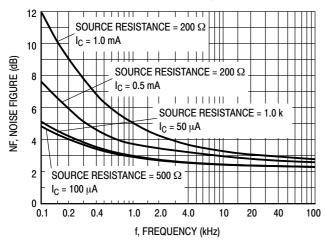


Figure 7. Storage Time

Figure 8. Fall Time

# TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}, Bandwidth = 1.0 \text{ Hz})$ 



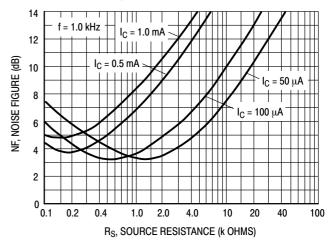
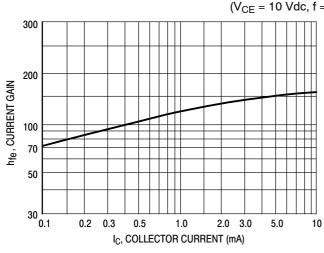


Figure 9.

Figure 10.

#### **h PARAMETERS**



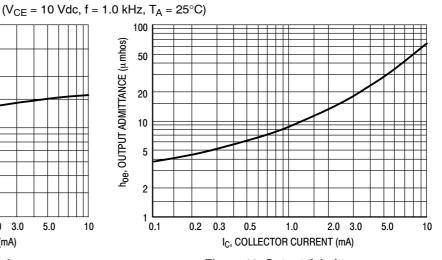


Figure 11. Current Gain

Figure 12. Output Admittance



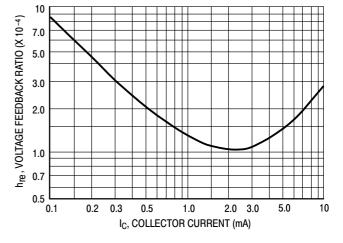


Figure 13. Input Impedance

Figure 14. Voltage Feedback Ratio

#### TYPICAL STATIC CHARACTERISTICS

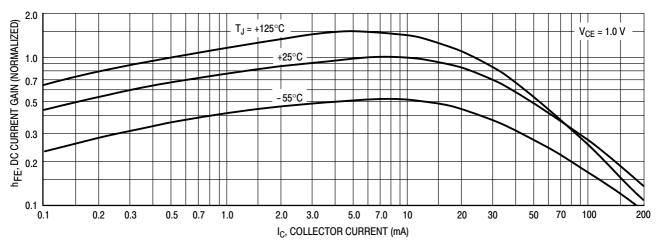


Figure 15. DC Current Gain

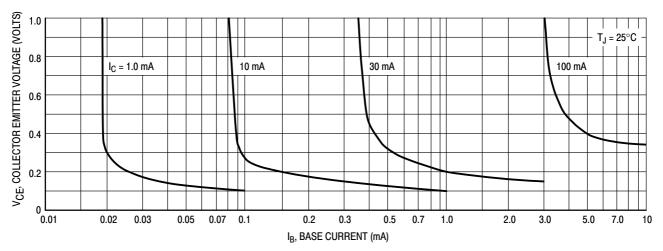


Figure 16. Collector Saturation Region

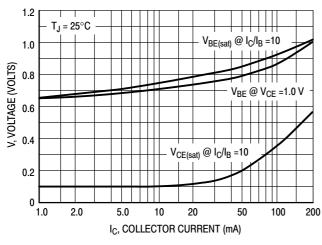


Figure 17. "ON" Voltages

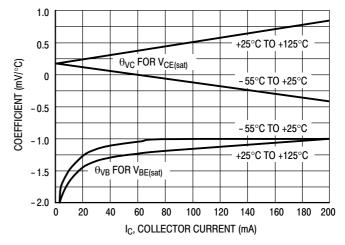
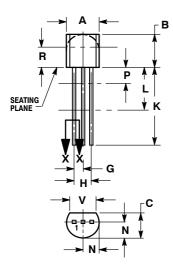


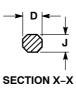
Figure 18. Temperature Coefficients

#### PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM** 



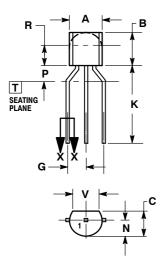
STRAIGHT LEAD **BULK PACK** 



#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
V	0 135		3 43	



**BENT LEAD** TAPE & REEL AMMO PACK



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
  CONTOUR OF PACKAGE BEYOND
- DIMENSION R IS UNCONTROLLED
- LEAD DIMENSION IS UNCONTROLLED IN PAND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93		
٧	3.43		

STYLE 1:

PIN 1 FMITTER

BASE

COLLECTOR

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